

NTD78N03

Power MOSFET

25 V, 78 A, Single N-Channel, DPAK

Features

- Low $R_{DS(on)}$
- Optimized Gate Charge
- Pb-Free Packages are Available

Applications

- Desktop VCORE
- DC-DC Converters
- Low Side Switch

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	25	V
Gate-to-Source Voltage			V _{GS}	± 20	V
Continuous Drain Current (Note 1)	Steady State	T _C = 25°C	I _D	14.8	A
		T _C = 85°C		11.5	
Power Dissipation (Note 1)		T _C = 25°C	P _D	2.3	W
Continuous Drain Current (Note 2)		T _C = 25°C	I _D	11.4	A
		T _C = 85°C		8.8	
Power Dissipation (Note 2)		T _C = 25°C	P _D	1.4	W
Continuous Drain Current (R _{θJC})		T _C = 25°C	I _D	78	A
		T _C = 85°C		56	
Power Dissipation (R _{θJC})		T _C = 25°C	P _D	64	W
Pulsed Drain Current	t _p = 10 μs		I _{DM}	210	A
Current Limited by Package		T _A = 25°C	I _{DmaxPkg}	45	A
Drain to Source dV/dt			dV/dt	8.0	V/ns
Operating Junction and Storage Temperature			T _J , T _{stg}	−55 to 175	°C
Source Current (Body Diode)			I _S	78	A
Single Pulse Drain-to-Source Avalanche Energy (V _{DD} = 24 V, V _{GS} = 10 V, L = 5.0 mH, I _{L(pk)} = 17 A, R _G = 25 Ω)			E _{AS}	722.5	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)			T _L	260	°C

THERMAL RESISTANCE

Junction-to-Case (Drain)	$R_{\theta JC}$	1.95	$^\circ\text{C/W}$
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	65	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	110	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

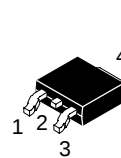
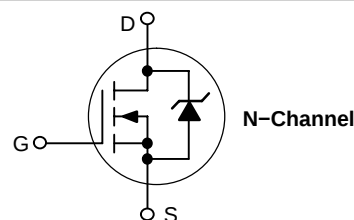
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size.



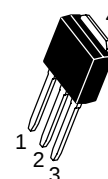
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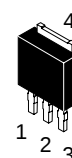
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
25 V	4.6 @ 10 V	78 A
	6.5 @ 4.5 V	



CASE 369AA
DPAK
(Bend Lead)
STYLE 2

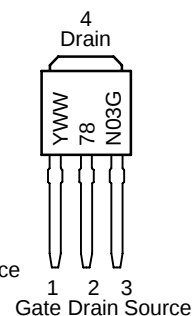
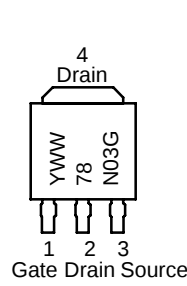
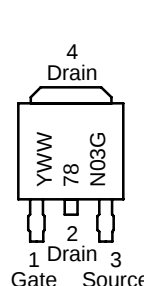


CASE 369D
DPAK
(Straight Lead)
STYLE 2



CASE 369AD
IPAK
(Straight Lead)

MARKING DIAGRAMS & PIN ASSIGNMENTS



Y = Year
WW = Work Week
78N03 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTD78N03

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			24		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V			1.5	μA
					10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0	1.6	3.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-5.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 78 A		4.6	6.0	mΩ
		V _{GS} = 4.5 V, I _D = 36 A		6.5	7.8	
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 15 A		22		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 12 V		1920	2250	pF
Output Capacitance	C _{oss}			960		
Reverse Transfer Capacitance	C _{rss}			420		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 20 V, I _D = 20 A		25.5	35	nC
Threshold Gate Charge	Q _{G(TH)}			2.4		
Gate-to-Source Charge	Q _{GS}			5.3		
Gate-to-Drain Charge	Q _{GD}			18.2		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DS} = 20 V, I _D = 20 A, R _G = 3.0 Ω		11		ns
Rise Time	t _r			68		
Turn-Off Delay Time	t _{d(off)}			23		
Fall Time	t _f			42		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.83	1.0	V
			T _J = 125°C		0.7		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /d _t = 100 A/μs, I _S = 20 A		39		ns	
Charge Time	t _a			17.8			
Discharge Time	t _b			21			
Reverse Recovery Time	Q _{RR}			33		nC	

PACKAGE PARASITIC VALUES

Source Inductance	L _S	Ta = 25C		2.49		nH
Drain Inductance	L _D			0.02		
Gate Inductance	L _G			3.46		
Gate Resistance	R _G			1.0		Ω

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

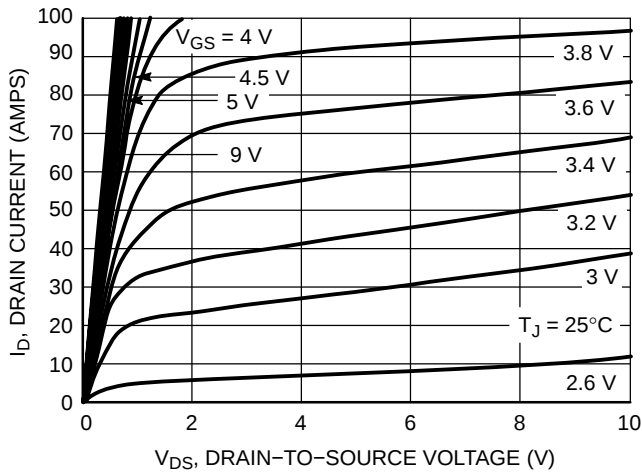


Figure 1. On-Region Characteristics

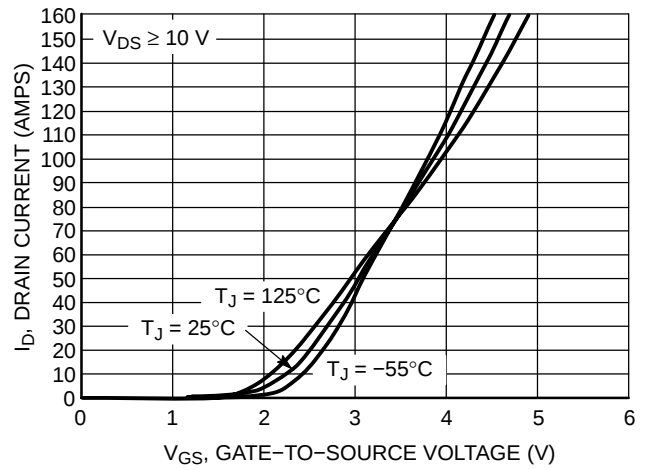


Figure 2. Transfer Characteristics

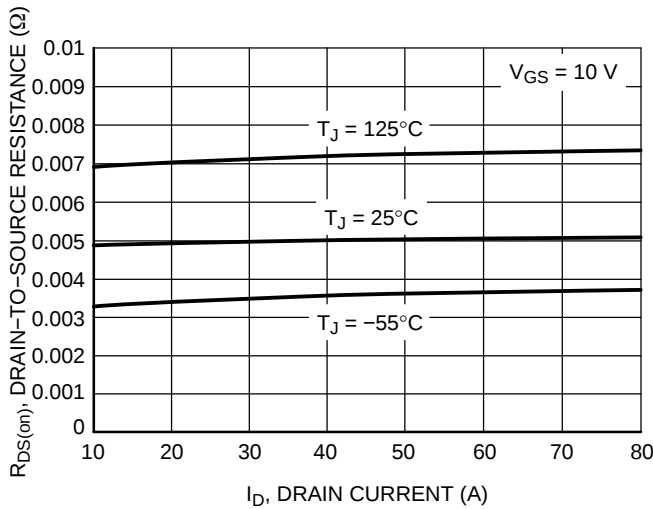


Figure 3. On-Resistance versus Drain Current and Temperature

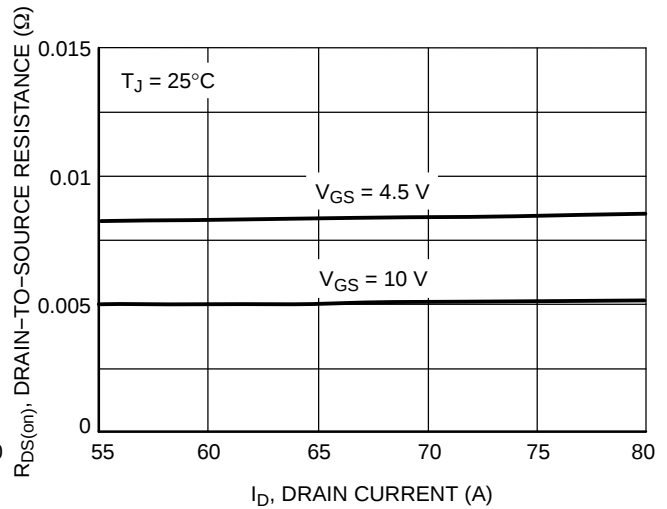


Figure 4. On-Resistance versus Drain Current and Gate Voltage

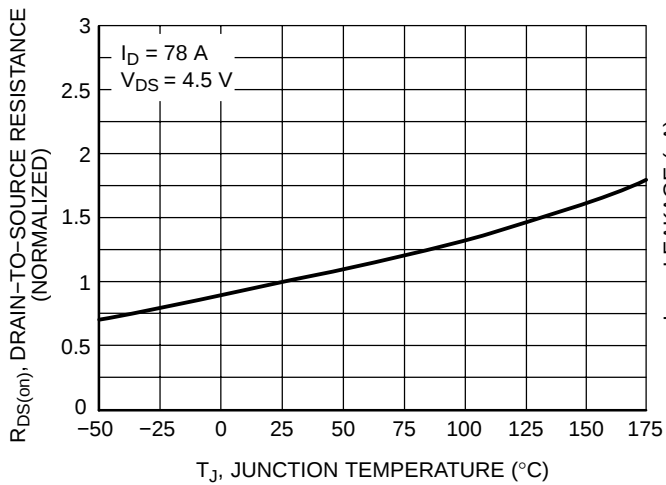


Figure 5. On-Resistance Variation with Temperature

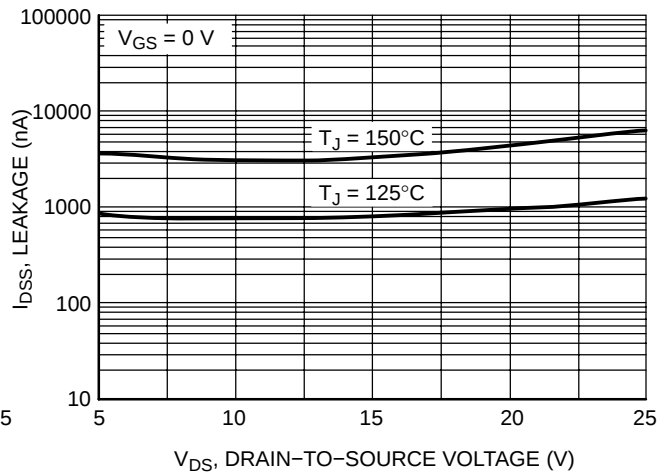
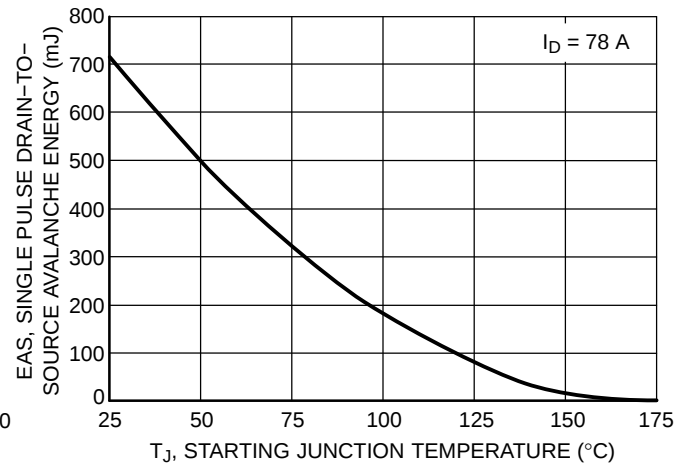
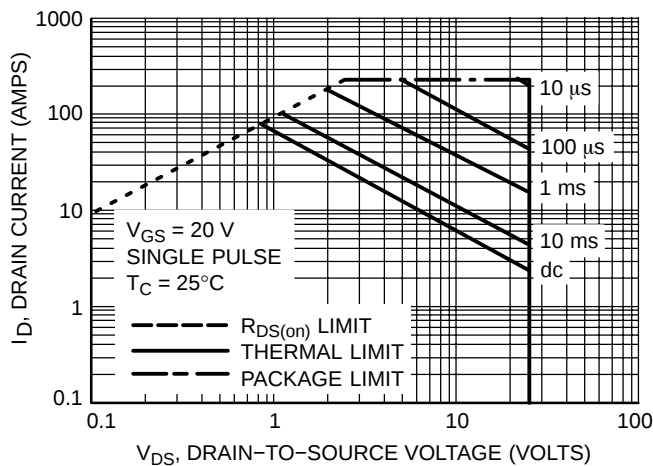
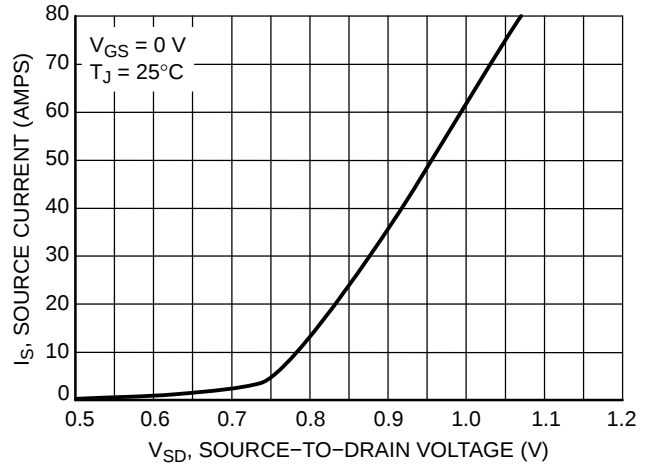
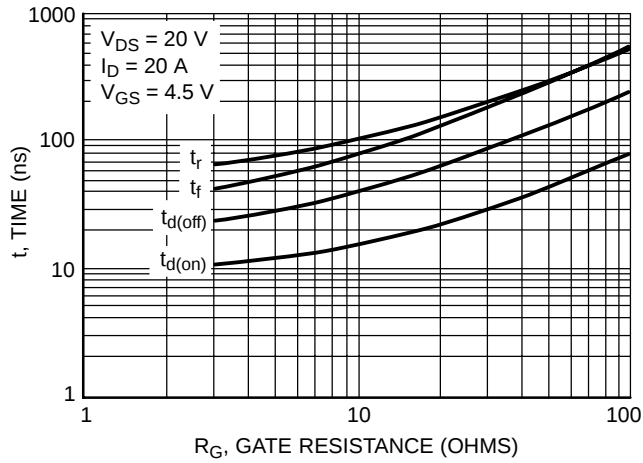
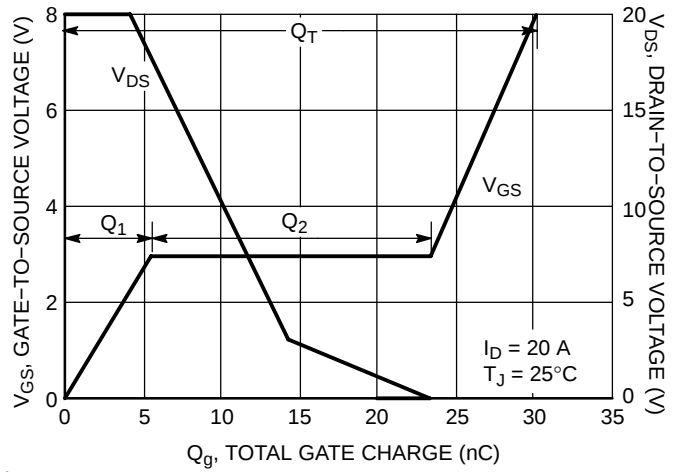
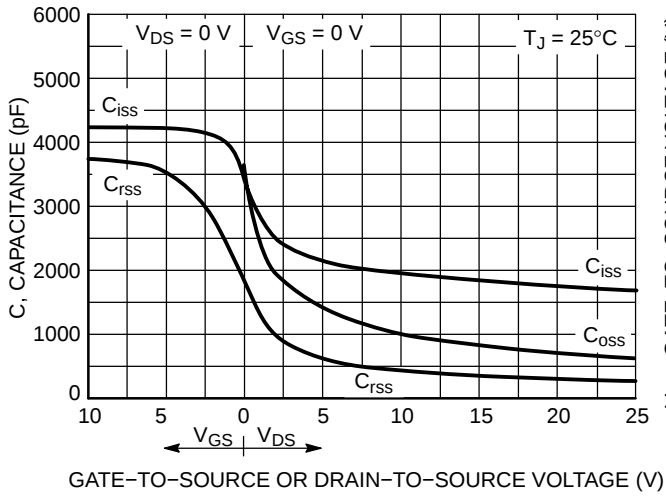
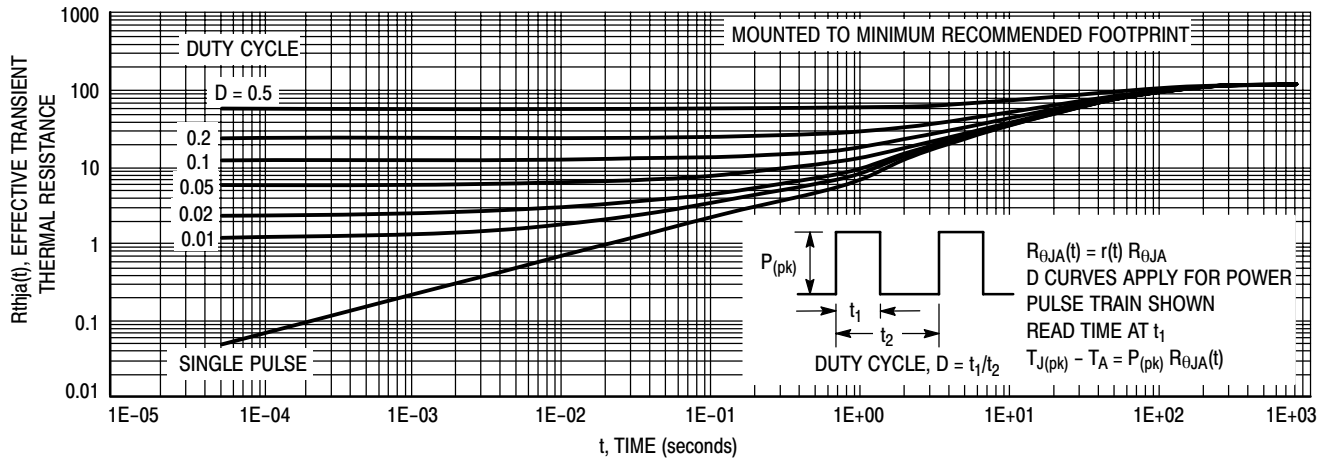


Figure 6. Drain-To-Source Leakage Current versus Voltage



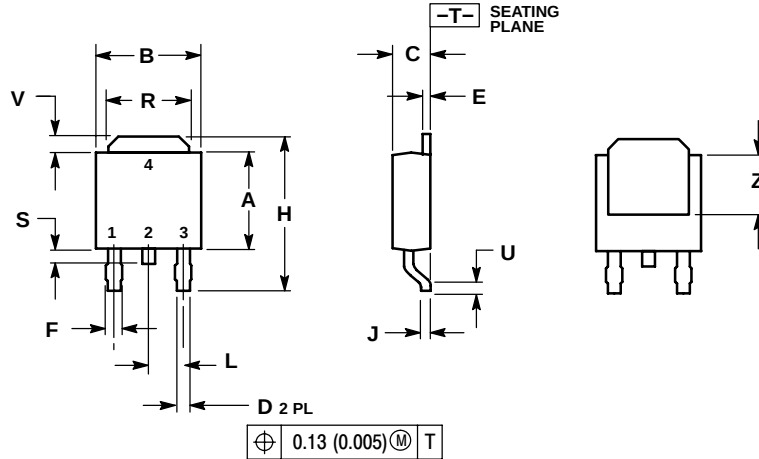


Order Number	Package	Shipping [†]
NTD78N03	DPAK	75 Units/Rail
NTD78N03G	DPAK (Pb-Free)	75 Units/Rail
NTD78N03T4	DPAK	2500 Tape & Reel
NTD78N03T4G	DPAK (Pb-Free)	
NTD78N03-1	DPAK Straight Lead	75 Units/Rail
NTD78N03-1G	DPAK Straight Lead (Pb-Free)	
NTD78N03-35	DPAK-3 Straight Lead (3.5 ± 0.15 mm)	75 Units/Rail
NTD78N03-35G	DPAK-3 Straight Lead (3.5 ± 0.15 mm) (Pb-Free)	

NTD78N03

PACKAGE DIMENSIONS

DPAK (SINGLE GUAGE) CASE 369AA-01 ISSUE A

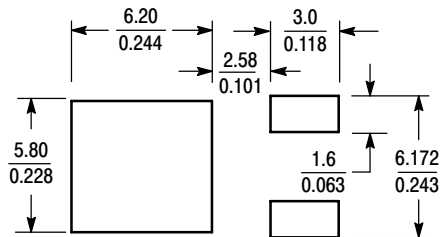


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
- PIN 1. GATE
 - DRAIN
 - SOURCE
 - DRAIN

SOLDERING FOOTPRINT*



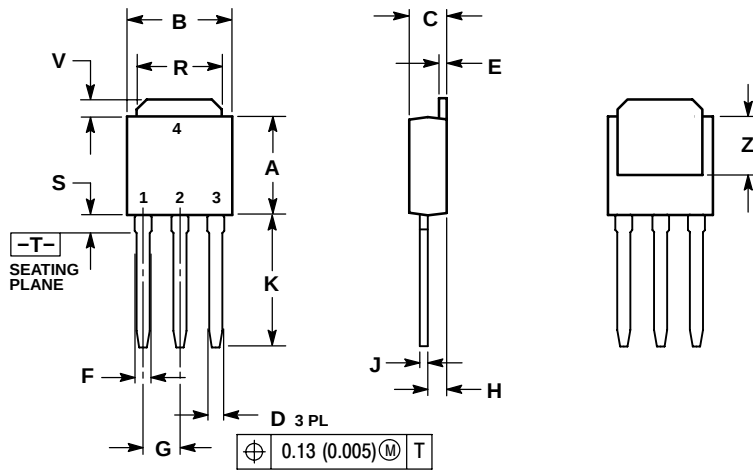
SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD78N03

PACKAGE DIMENSIONS

DPAK CASE 369D-01 ISSUE B



NOTES:

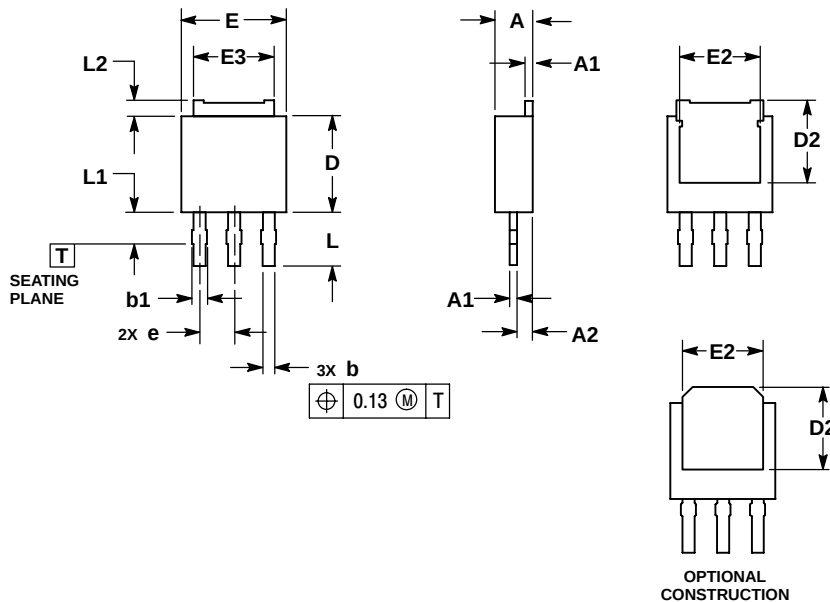
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

3.5 MM IPAK, STRAIGHT LEAD CASE 369AD-01 ISSUE O



NOTES:

- 1.. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2.. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL TIP.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD GATE OR MOLD FLASH.

DIM	MILLIMETERS	
	MIN	MAX
A	2.19	2.38
A1	0.46	0.60
A2	0.87	1.10
b	0.69	0.89
b1	0.77	1.10
D	5.97	6.22
D2	4.80	---
E	6.35	6.73
E2	4.70	---
E3	4.45	5.46
e	2.28 BSC	
L	3.40	3.60
L1	---	2.10
L2	0.89	1.27

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